

A3400

N-Channel Enhancement Mode MOSFET



Features

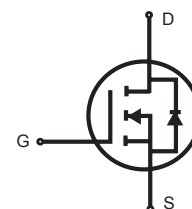
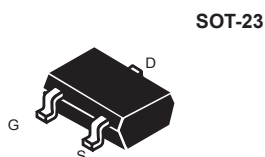
- High performance trench technology
- Low ON-resistance
- Low profile surface mount package
- Lead (Pb) free product

Product Summary

V _{DS} (V)	I _D (A)	R _{DS(ON)} (mΩ) Max
30V	3.5A	45 @V _{GS} = 10V
		65 @V _{GS} = 2.5V

Applications

- Load switch
- PWM application
- Power management



Absolute Maximum Ratings (T_A = 25°C unless otherwise noted)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	V _{GS}	± 20	V
Drain Current-Continuous @ T _C = 25°C	I _D	3.5	A
-Pulsed ^b	I _{DM}	13	A
Drain-Source Diode Forward Current ^a	I _S	1.25	A
Maximum Power Dissipation ^a	P _D	1.25	W
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to 150	°C

Thermal Characteristics

Thermal Resistance, Junction-to-Ambient ^a	R _{θJA}	100	°C/W
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Electrical Characteristics (TA = 25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ ^c	Max	Unit
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250 μA	30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =24V, V _{GS} =0V			1	μA
Gate-Body Leakage	I _{GSS}	V _{GS} =±20V, V _{DS} =0V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} I _D =250 μA	1	1.7	3.0	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =3.5A		35	45	mΩ
		V _{GS} =4.5V, I _D =2A		50	65	
On-State Drain Current	I _{D(on)}	V _{DS} =5V, V _{GS} =10V	6			A
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =3.5A		5		S
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _D =1.25A		0.8	1.2	V

Dynamic

Input Capacitance	C _{ISS}	V _{DS} =15V V _{GS} =0V f=1.0MHz		650		pF
Output Capacitance	C _{OSS}			250		
Reverse Transfer Capacitance	C _{RSS}			110		
Turn-On Delay Time	t _{D(on)}	V _D =10V, I _D =1A, V _{GS} =10V, R _{GEN} =6Ω, R _L =10Ω		20		ns
Rise Time	t _r			12		
Turn-Off Delay Time	t _{D(off)}			20		
Fall Time	t _f			10		
Total Gate Charge	Q _g	V _{DS} =10V, I _D =3.5A, V _{GS} =4.5V		8		nC
Gate-Source Charge	Q _{gs}			4		
Gate-Drain Charge	Q _{gd}			2.5		

Notes:

- Surface Mounted on FR4 Board, t ≤ 10 sec.
- Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
- Guaranteed by design, not subject to production testing.

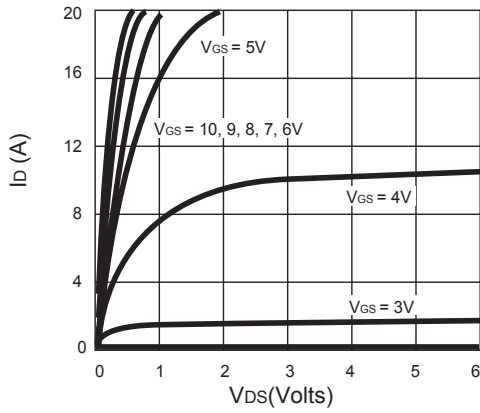


Figure 1. On-Regions Characteristics

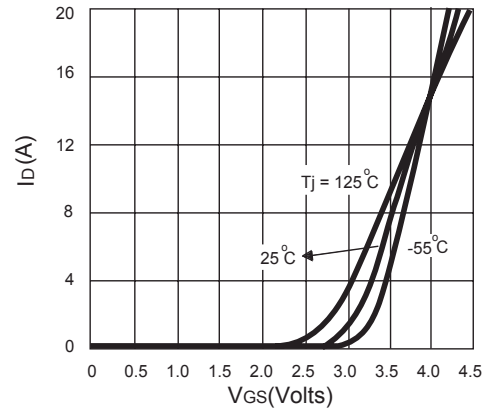


Figure 2. Transfer Characteristics

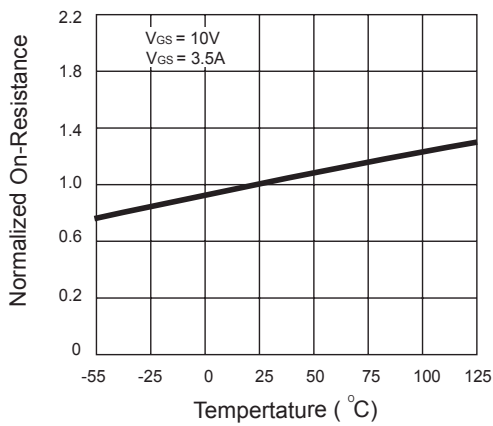


Figure 3. On-Resistance vs. Junction Temperature

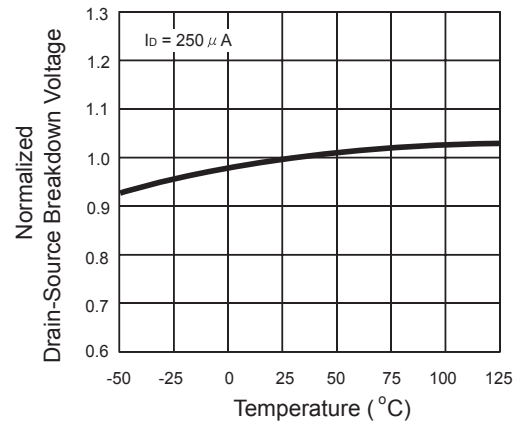


Figure 4. Drain-Source Breakdown Voltage vs. Temperature

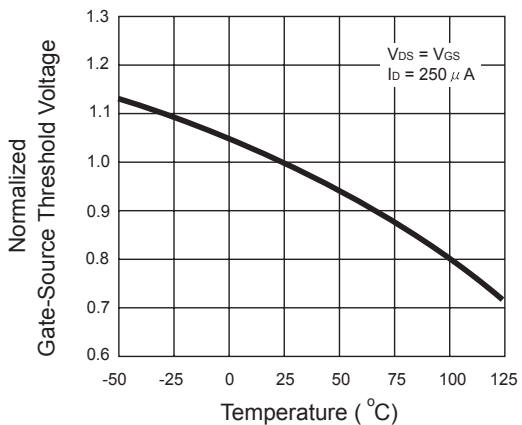


Figure 5. Gate Threshold vs Junction Temperature

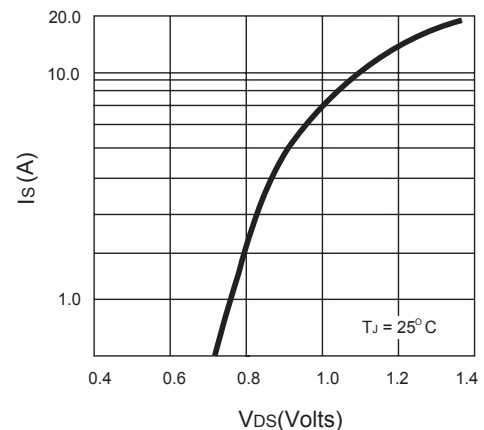


Figure 6. Body Diode Characteristics

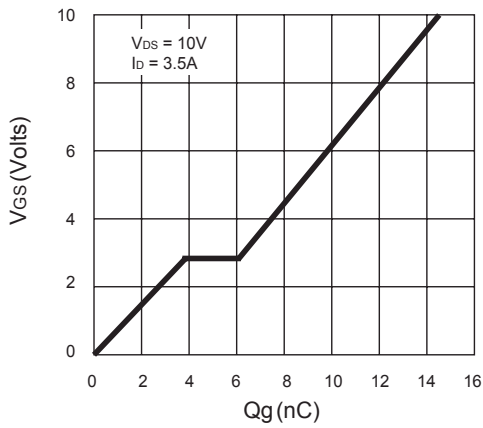


Figure 7. Gate-Charge Characteristics

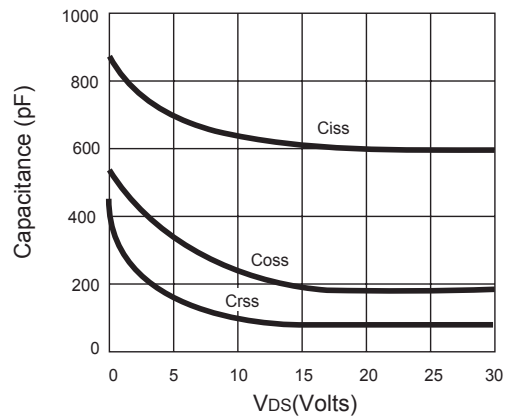


Figure 8. Capacitance Characteristics

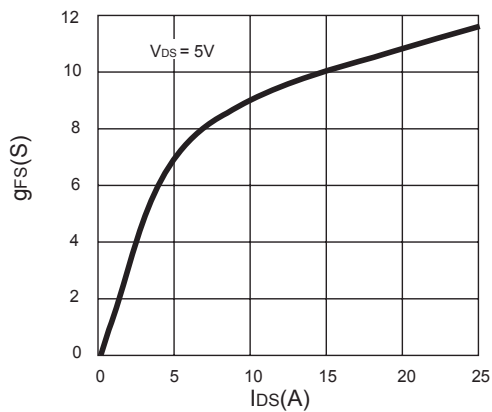


Figure 9. Transconductance vs. Drain Current

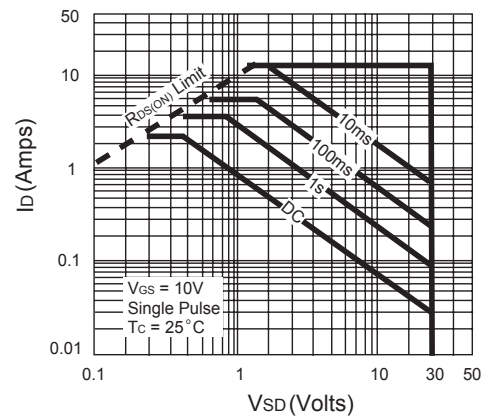


Figure 10. Maximum Forward Biased Safe Operating Area

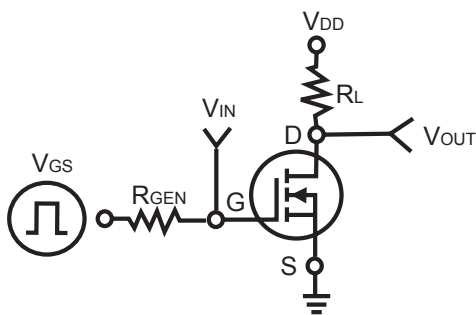


Figure 11. Switching Test Circuit

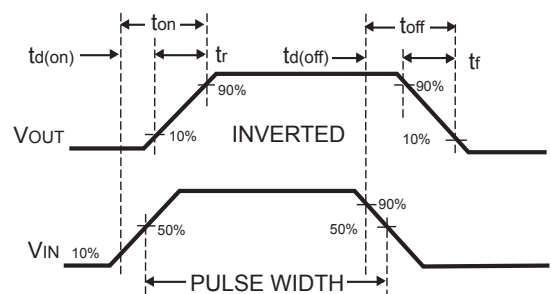


Figure 12. Switching Waveforms

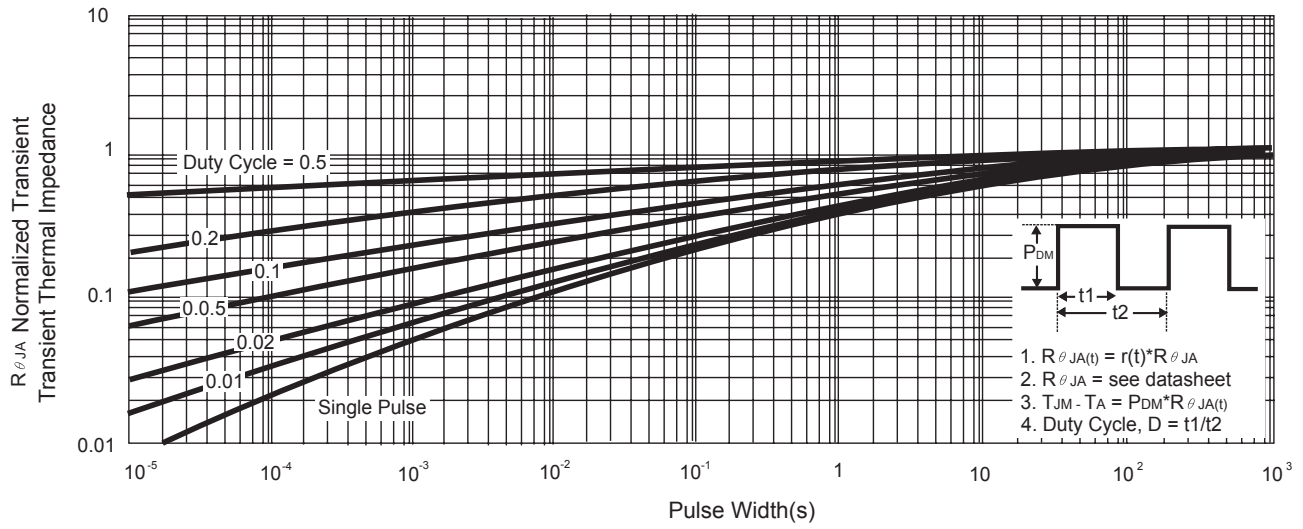


Figure 13. Normalized Maximum Transient Thermal Impedance